

650V 60A Insulated Gate Bipolar Transistor
AKB65A060UCH

Description:

Gen 3 IGBT with soft, fast recovery half current rated anti-parallel Emitter Controlled diode, providing ultra-low conduction loss. They are designed for applications such as UPS, inverters, welding machines, etc.

Features:

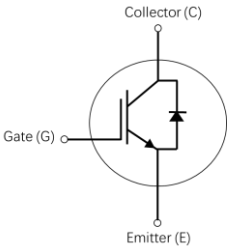
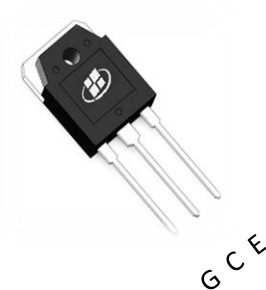
- Easy paralleling capability due to positive temperature coefficient in V_{CESAT}
- Low EMI
- Low Gate Charge
- Very soft, fast recovery diode
- Maximum junction temperature $T_{VJmax} = 175^{\circ}C$
- RoHS compliant
- Halogen-free

Applications:

- Industrial UPS
- Charger
- Energy Storage
- Three-Phase Solar String Inverter
- Welding machines

Key Performance Parameters:

Parameter	Value	Unit
V_{CE}	650	V
$V_{CESAT}, T_{VJ} = 25^{\circ}C$	1.6	V
I_C	60	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AKB65A060UCH	TO-3P	B65A060UCH	Tube	See the detail package information

Maximum Ratings ($T_{VJ} = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CE}	Collector - Emitter Voltage	650	V
I_C	Collector Current - Continuous ($T_C = 25^{\circ}\text{C}$) ^(Note 1)	120	A
	Collector Current - Continuous ($T_C = 100^{\circ}\text{C}$)	60	A
I_{CM}	Collector Current - Pulsed ^(Note 2)	240	A
I_F	Diode Forward Current, Limited by T_{VJmax} ($T_C = 25^{\circ}\text{C}$)	60	A
	Diode Forward Current, Limited by T_{VJmax} ($T_C = 100^{\circ}\text{C}$)	30	A
I_{FM}	Diode Pulsed Current - Pulsed ^(Note 2)	120	A
V_{GE}	Gate - Emitter Voltage	± 20	V
	Transient Gate - Emitter Voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	± 30	
P_D	Power Dissipation ($T_C = 25^{\circ}\text{C}$)	300	W
	Power Dissipation ($T_C = 100^{\circ}\text{C}$)	150	W
T_{VJ}	Operating Junction Temperature Range	-40 to +175	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	IGBT Thermal Resistance, Junction - to - Case, Steady - State	0.5	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Diode Thermal Resistance, Junction - to - Case, Steady - State	0.9	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction - to - Ambient Steady State	40	$^{\circ}\text{C/W}$

Notes:

- 1. The max collector current rating is package limited
- 2. Repetitive rating: pulse width limited by maximum junction temperature

Electrical Characteristics ($T_{VJ} = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 0.2\text{ mA}$	650			V
V_{CESAT}	Collector-Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 60\text{ A}$		1.70	2.10	V
		$V_{GE} = 15\text{ V}, I_C = 60\text{ A}, T_{VJ} = 125^{\circ}\text{C}$		1.98		
		$V_{GE} = 15\text{ V}, I_C = 60\text{ A}, T_{VJ} = 175^{\circ}\text{C}$		2.10		
V_F	Diode Forward Voltage	$V_{GE} = 0\text{ V}, I_F = 30\text{ A}$		1.38	1.70	V
		$V_{GE} = 0\text{ V}, I_F = 30\text{ A}, T_{VJ} = 125^{\circ}\text{C}$		1.28		
		$V_{GE} = 0\text{ V}, I_F = 30\text{ A}, T_{VJ} = 175^{\circ}\text{C}$		1.22		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{CE} = V_{GE}, I_C = 0.5\text{ mA}$	3.2	4.0	4.8	V
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}$			50	μA
		$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}, T_{VJ} = 175^{\circ}\text{C}$		2000		
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$			± 100	nA
g_{fs}	Transconductance	$V_{CE} = 20\text{ V}, I_C = 60\text{ A}$		60		S
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V},$ $F = 1\text{ MHz}$		2020		pF
C_{oes}	Output Capacitance			114		pF
C_{res}	Reverse Transfer Capacitance			18		pF
Q_G	Total Gate Charge	$V_{CC} = 520\text{ V}, I_C = 60\text{ A},$ $V_{GE} = 15\text{ V}$		67		nC
Q_{GE}	Gate-Emitter Charge			10		nC
Q_{GC}	Gate-Collector Charge			21		nC
L_E	Internal Emitter Inductance			13		nH
Switching Characteristics, Inductive Load ($T_{VJ} = 25^{\circ}\text{C}$)						
$t_{d(on)}$	Turn On Delay Time	$V_{CC} = 400\text{ V}$ $I_C = 60\text{ A}$ $V_{GE} = 15\text{ V}$ $R_{Gon} = 12\ \Omega$ $R_{Goff} = 12\ \Omega$		18		ns
t_r	Rise Time			36		ns
$t_{d(off)}$	Turn Off Delay Time			130		ns
t_f	Fall Time			39		ns
E_{on}	Turn On Energy			1.80		mJ
E_{off}	Turn Off Energy			0.75		mJ
E_{ts}	Total Switching Energy			2.55		mJ

$t_{d(on)}$	Turn On Delay Time	$V_{CC} = 400\text{ V}$ $I_C = 30\text{ A}$ $V_{GE} = 15\text{ V}$ $R_{G(on)} = 12\ \Omega$ $R_{G(off)} = 12\ \Omega$		19		ns
t_r	Rise Time			15		ns
$t_{d(off)}$	Turn Off Delay Time			141		ns
t_f	Fall Time			23		ns
E_{on}	Turn On Energy			0.72		mJ
E_{off}	Turn Off Energy			0.38		mJ
E_{ts}	Total Switching Energy			1.10		mJ

Diode Characteristics ($T_{VJ} = 25^\circ\text{C}$)

t_{rr}	Reverse Recovery Time	$V_R = 400\text{ V}, I_F = 60\text{ A},$ $di/dt = 1000\text{ A}/\mu\text{s}$		187		ns
Q_{rr}	Reverse Recovery Charge			1.8		μC
I_{rrm}	Peak Reverse Recovery Current			15.4		A
di_{rr}/dt	Diode Peak Rate of Fall of Reverse Recovery Current			-441		A/ μs

t_{rr}	Reverse Recovery Time	$V_R = 400\text{ V}, I_F = 30\text{ A},$ $di/dt = 1000\text{ A}/\mu\text{s}$		112		ns
Q_{rr}	Reverse Recovery Charge			1.24		μC
I_{rrm}	Peak Reverse Recovery Current			14		A
di_{rr}/dt	Diode Peak Rate of Fall of Reverse Recovery Current			-617		A/ μs

Switching Characteristics, Inductive Load ($T_{VJ} = 150^\circ\text{C}$)

$t_{d(on)}$	Turn On Delay Time	$V_{CC} = 400\text{ V}$ $I_C = 60\text{ A}$ $V_{GE} = 15\text{ V}$ $R_{G(on)} = 12\ \Omega$ $R_{G(off)} = 12\ \Omega$		18		ns
t_r	Rise Time			34		ns
$t_{d(off)}$	Turn Off Delay Time			148		ns
t_f	Fall Time			38		ns
E_{on}	Turn On Energy			2.50		mJ
E_{off}	Turn Off Energy			1.20		mJ
E_{ts}	Total Switching Energy			3.70		mJ

$t_{d(on)}$	Turn On Delay Time	$V_{CC} = 400\text{ V}$ $I_C = 30\text{ A}$ $V_{GE} = 15\text{ V}$ $R_{G(on)} = 12\ \Omega$ $R_{G(off)} = 12\ \Omega$		18		ns
t_r	Rise Time			16		ns
$t_{d(off)}$	Turn Off Delay Time			173		ns
t_f	Fall Time			47		ns
E_{on}	Turn On Energy			1.26		mJ
E_{off}	Turn Off Energy			0.48		mJ
E_{ts}	Total Switching Energy			1.74		mJ

Diode Characteristics ($T_{VJ} = 150^{\circ}\text{C}$)

t_{rr}	Reverse Recovery Time	$V_R = 400\text{ V}, I_F = 60\text{ A},$ $di/dt = 1000\text{ A}/\mu\text{s}$		291		ns
Q_{rr}	Reverse Recovery Charge			4.5		μC
I_{rrm}	Peak Reverse Recovery Current			26.8		A
di_{rr}/dt	Diode Peak Rate of Fall of Reverse Recovery Current			-614		$\text{A}/\mu\text{s}$

t_{rr}	Reverse Recovery Time	$V_R = 400\text{ V}, I_F = 30\text{ A},$ $di/dt = 1000\text{ A}/\mu\text{s}$		220		ns
Q_{rr}	Reverse Recovery Charge			2.1		μC
I_{rrm}	Peak Reverse Recovery Current			25		A
di_{rr}/dt	Diode Peak Rate of Fall of Reverse Recovery Current			-662		$\text{A}/\mu\text{s}$

Electrical Characteristics Diagrams

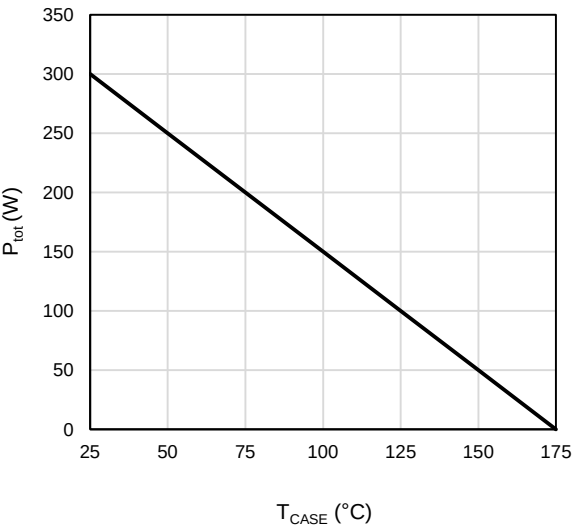


Figure 1: Power De-rating

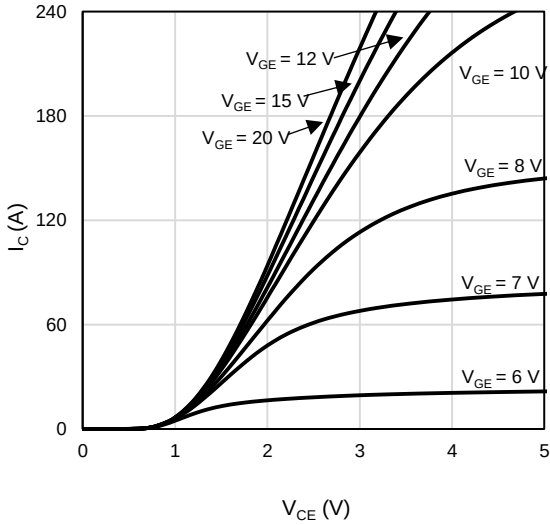


Figure 2: Typical Output Characteristics
($T_{VJ} = 25^{\circ}C$)

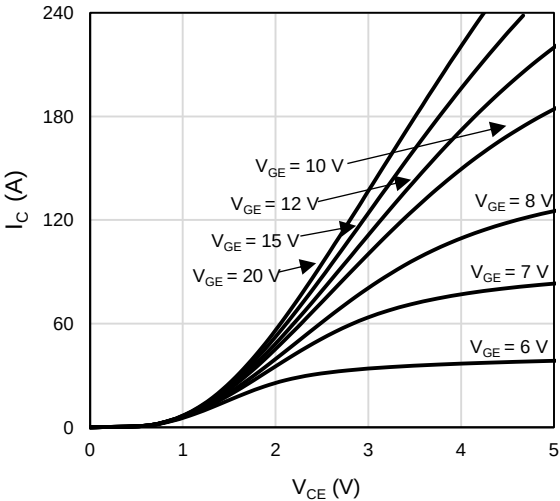


Figure 3: Typical Output Characteristics
($T_{VJ} = 150^{\circ}C$)

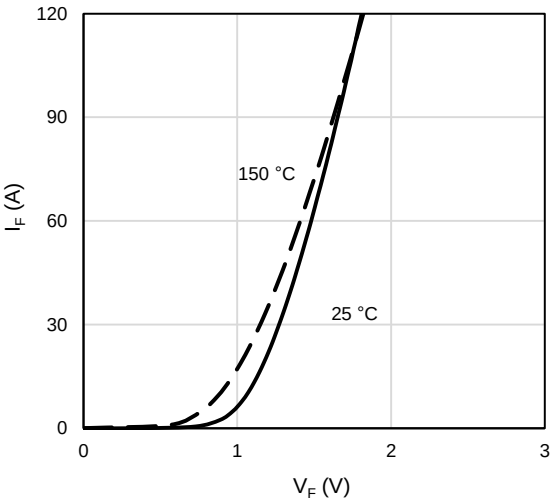


Figure 4: Diode Forward Current Characteristics

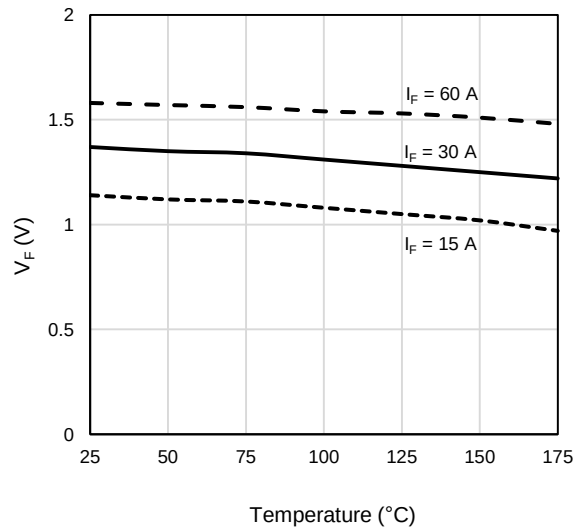


Figure 5: Diode Forward Voltage vs. Junction Temperature

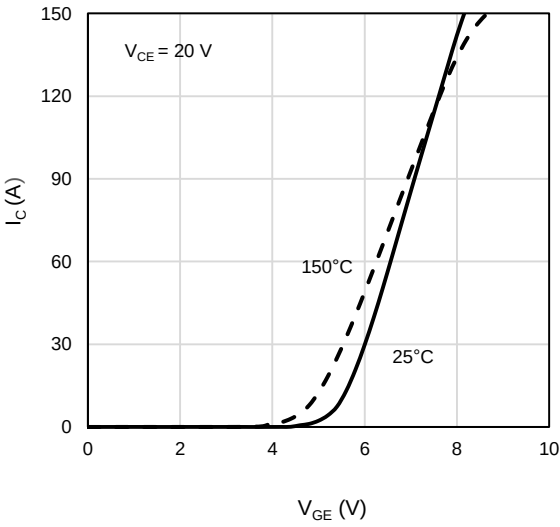


Figure 6: Transfer Characteristics

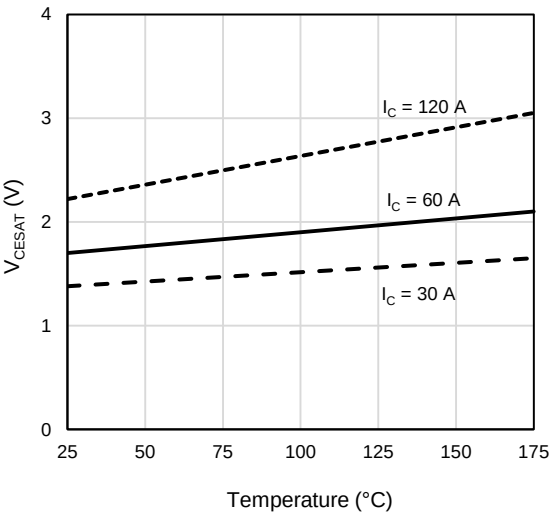


Figure 7: Collect-emitter saturation voltage vs. Junction Temperature

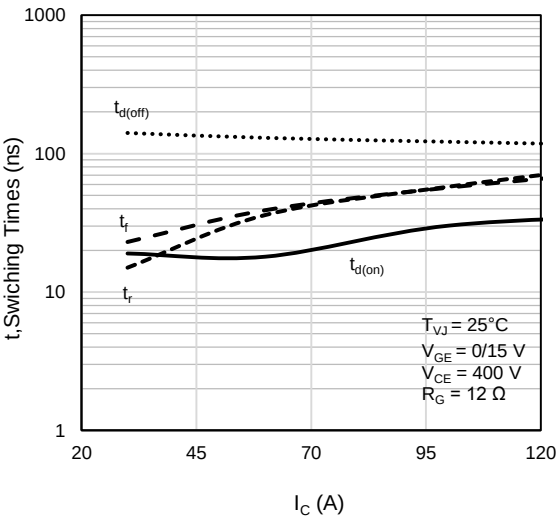


Figure 8: Switching Times vs. Collector Current

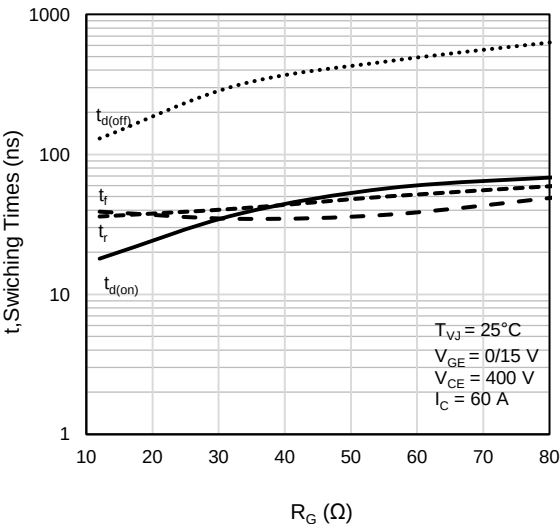


Figure 9: Switching Times vs. Gate Resistor

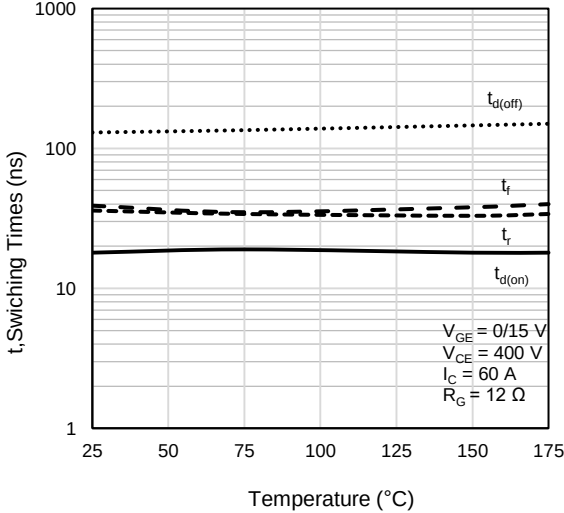


Figure 10: Switching Times vs. Junction Temperature

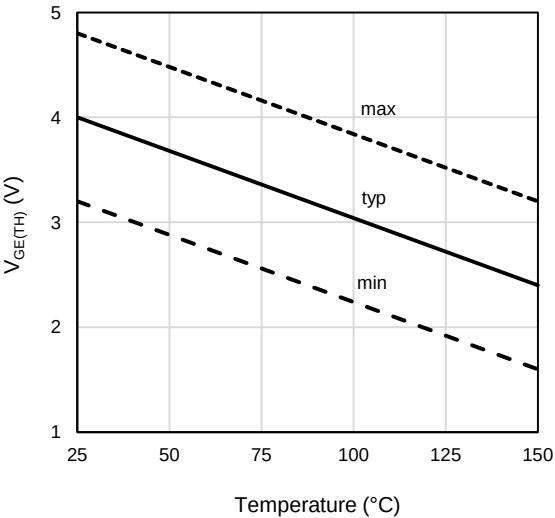


Figure 11: Threshold voltage vs. Junction Temperature

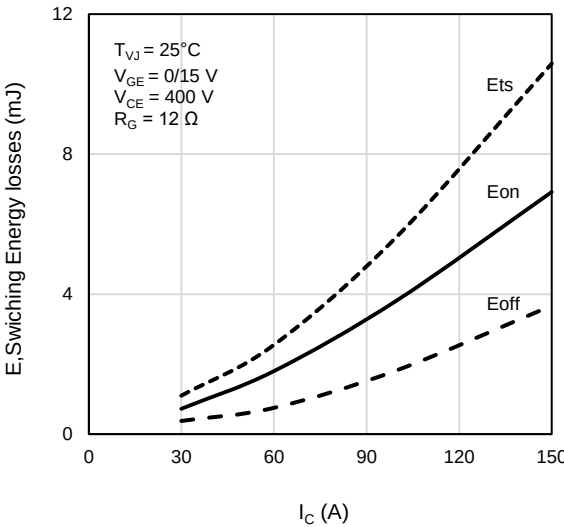


Figure 12: Switching Energy losses vs. Collector Current

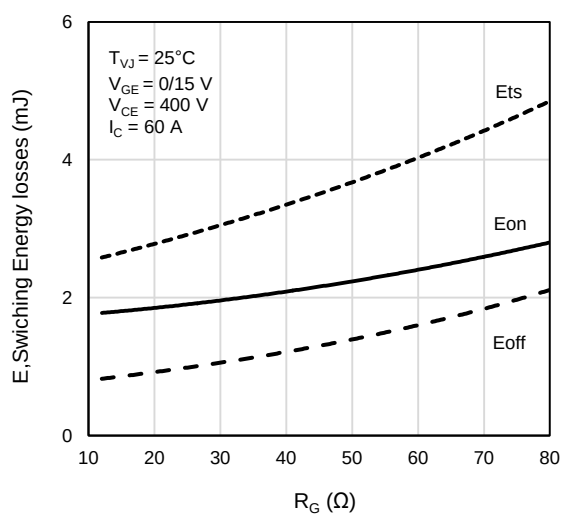


Figure 13: Switching Energy losses vs. Gate Resistor

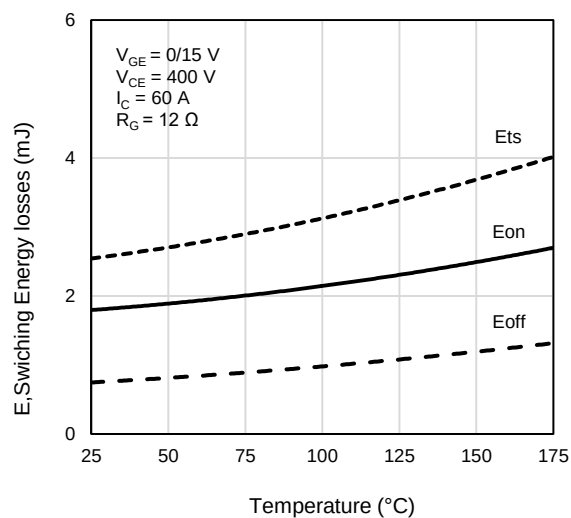


Figure 14: Switching Energy losses vs. Junction Temperature

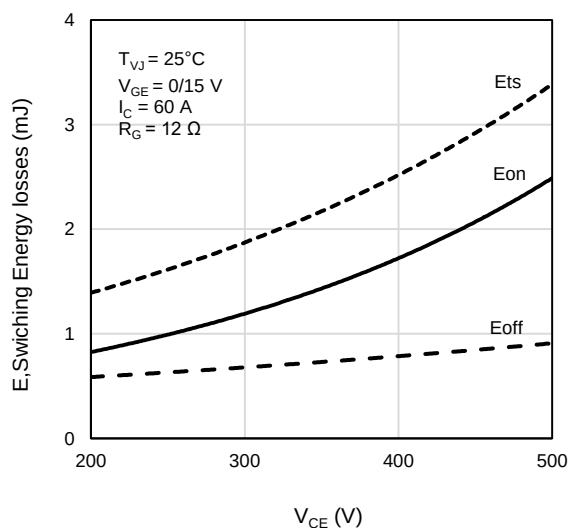


Figure 15: Switching Energy losses vs. Collector Emitter Voltage

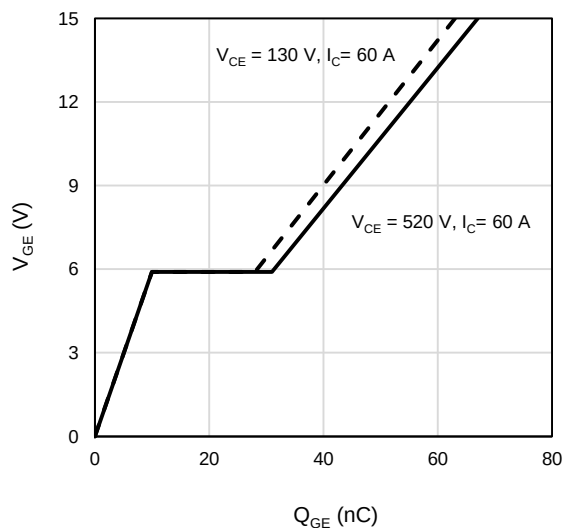


Figure 16: Gate-Charge Characteristics

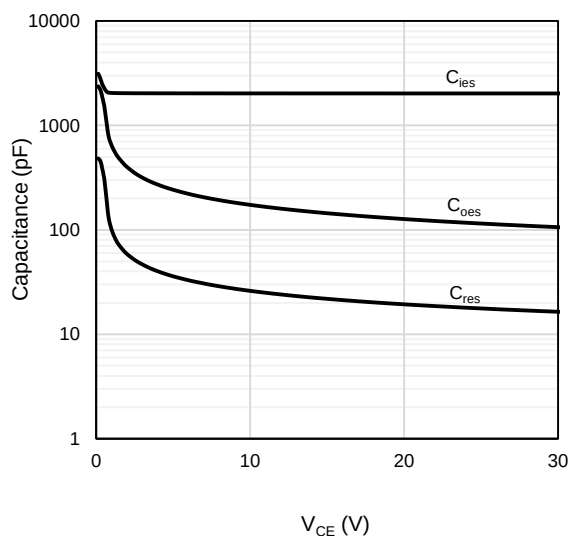


Figure 17: Capacitance Characteristics

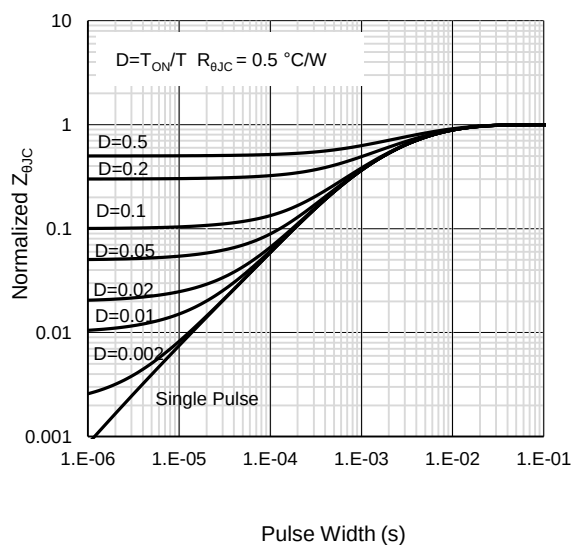
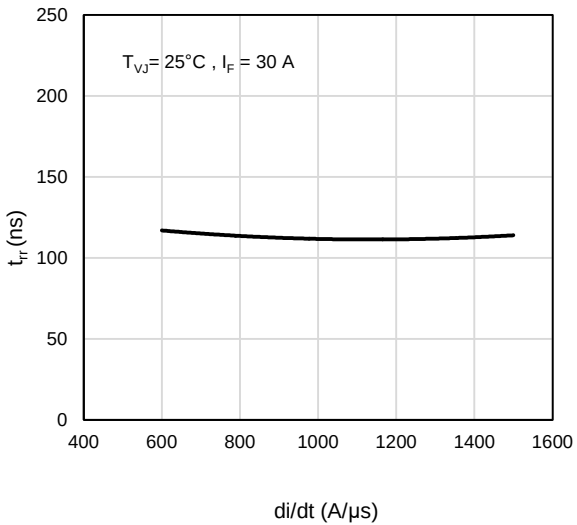
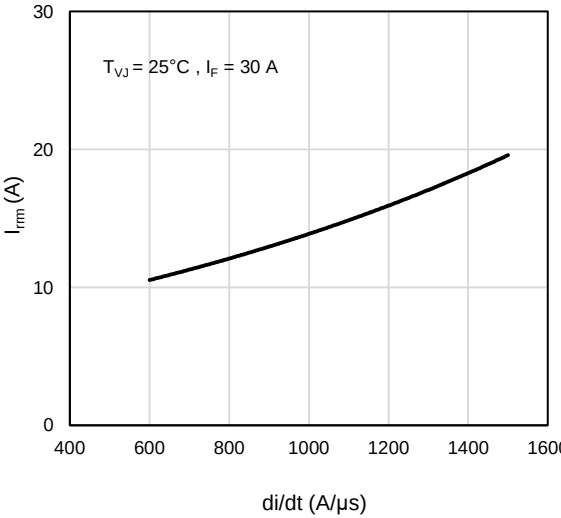
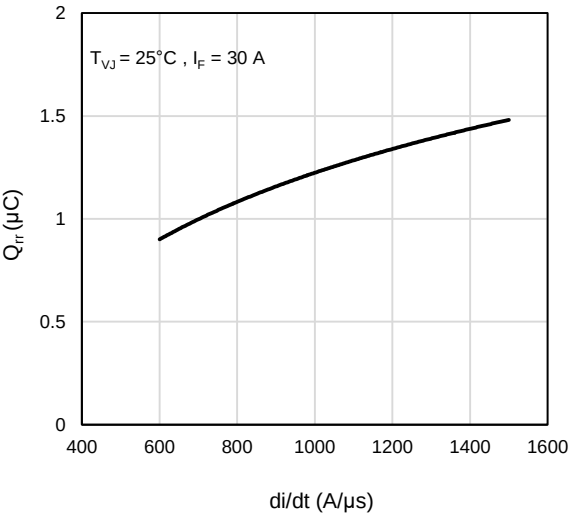
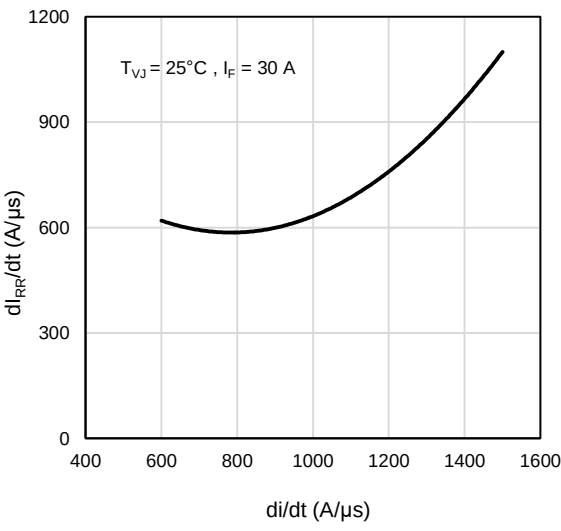
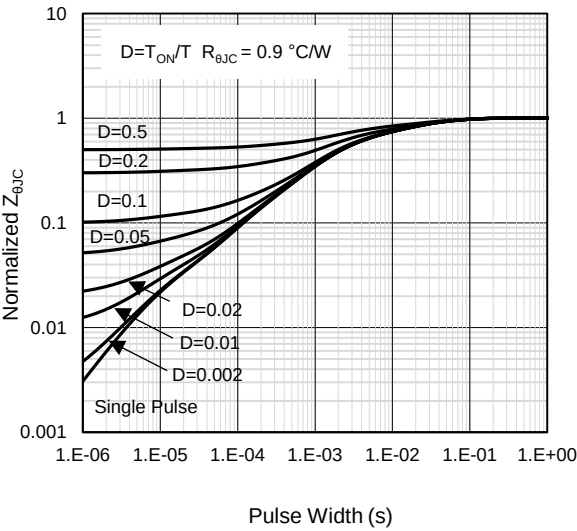
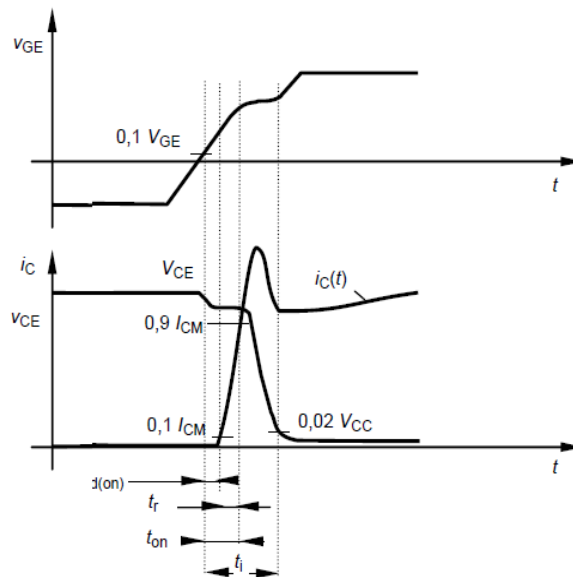
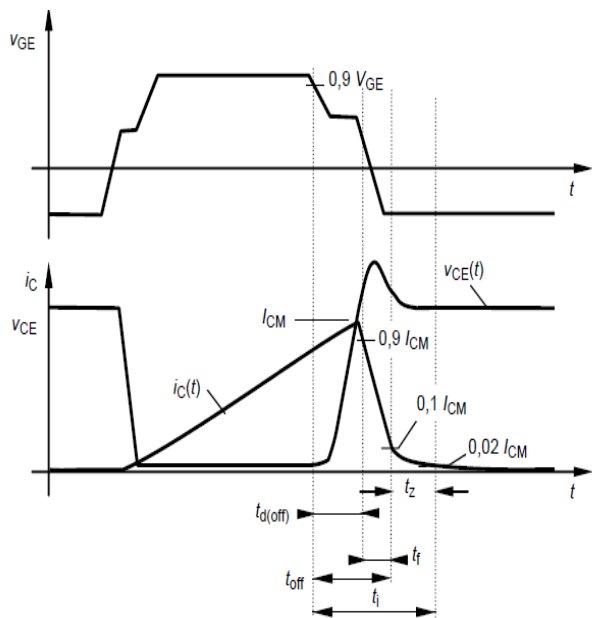


Figure 18: Normalized Maximum IGBT Transient Thermal Impedance

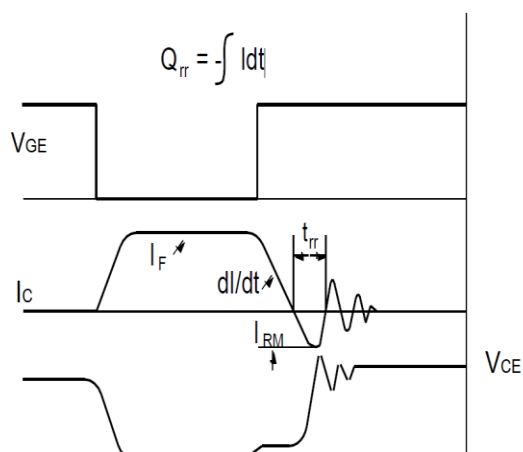
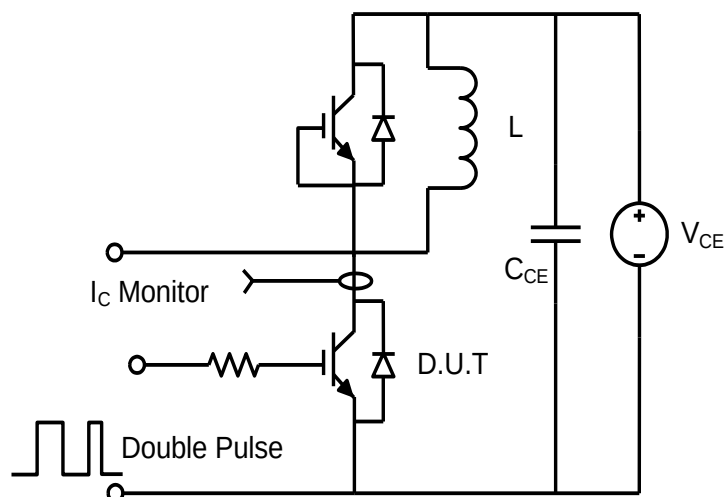


Test Circuit and Waveform

Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Revision History

Revision	Released	Remark
Rev.1.1	2025	

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements, the information described or contained herein may be changed without prior notice.